NSN 5961-01-342-8402

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-342-8402 **Inclosure Material:** Plastic **Overall Length:** Between 0.135 inches and 0.185 inches **Terminal Length:** Between 0.505 inches and 0.750 inches **Overall Height:** Between 0.080 inches and 0.125 inches **Overall Width:** Between 0.110 inches and 0.130 inches **Function For Which Designed:** Phototransistor **End Application:** 6625-01-235-0428 multimeter **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 60.0 breakdown voltage, collector-to-emitter, base open **Current Rating Per Characteristic:** 100.00 nanoamperes repetitive peak forward current peak **Power Rating Per Characteristic:** 150.0 milliwatts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius junction **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli

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